

AMENDMENT

IN THE SPECIFICATION:

Page 7, replace the paragraph beginning at line 16 with the following paragraph:

In one embodiment of the present invention, the high-vapor pressure liquid is sprayed onto the surface of a semiconductor wafer at a temperature of 30°-50°C. The liquid may be sprayed either as a thick film or as a thin layer. The layer is preferably at least 5-10 Δ (angstroms) thick. It is preferably sprayed using a misting nozzle made of Teflon used in wet benches for spraying deionized water onto wafer surfaces. However, any other nozzle used in the art may be employed. The wafer is preferably covered with the liquid for at least one minute and preferably up to 10 minutes. The liquid may be applied to the surface once during this time period or it may be sprayed multiple times to ensure that the wafer surface remains wet. As well, the wafer may be rotated at approximately 100 rpm while the liquid is sprayed on it to ensure uniform coverage of the wafer surface.

Page 9, replace the paragraph beginning at line 15 with the following paragraph:

In post-etch cleaning applications, cryogenic particles cannot get inside the high aspect ratio features of vias and trenches. Gas or vapor is needed to diffuse into these features effectively. The gas or vapor will then chemically react with the polymeric residue and convert it to gaseous by-products which can be removed from the surface by a flow of nitrogen across the substrate surface. Alternatively, it can be introduced in a separate chamber kept under low pressure. The gas/vapor phase reaction in this chamber could be done at temperatures of up to ~~200EC~~ 200°C. Following this cleaning process, the wafers may be transferred to a second cleaning chamber at atmospheric pressure where the cryogenic cleaning takes place.

Page 12, delete the last paragraph beginning at line 17 with the heading "References".